



US006999134B2

(12) **United States Patent**
Lee et al.

(10) **Patent No.:** **US 6,999,134 B2**
(45) **Date of Patent:** **Feb. 14, 2006**

(54) **LIQUID CRYSTAL DISPLAY AND THIN
FILM TRANSISTOR ARRAY PANEL
THEREFOR**

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(*) Notice: Subject to any disclaimer, the term of this
patent is extended or adjusted under 35
U.S.C. 154(b) by 0 days.

(21) Appl. No.: **10/445,849**

(22) Filed: **May 28, 2003**

(65) **Prior Publication Data**

US 2004/0094766 A1 May 20, 2004

(30) **Foreign Application Priority Data**

Nov. 14, 2002 (KR) 10-2002-0070706

(51) **Int. Cl.**
G02F 1/1343 (2006.01)

(52) **U.S. Cl.** **349/38; 349/42; 257/57**

(58) **Field of Classification Search** 257/72,
257/59, 350, 347, 753, 754, 351, 50, 51,
257/52, 53; 349/33, 38, 39, 42, 43, 46, 47

See application file for complete search history.

(56) **References Cited**

U.S. PATENT DOCUMENTS

6,320,204 B1 * 11/2001 Hirabayashi et al. 257/71

* cited by examiner

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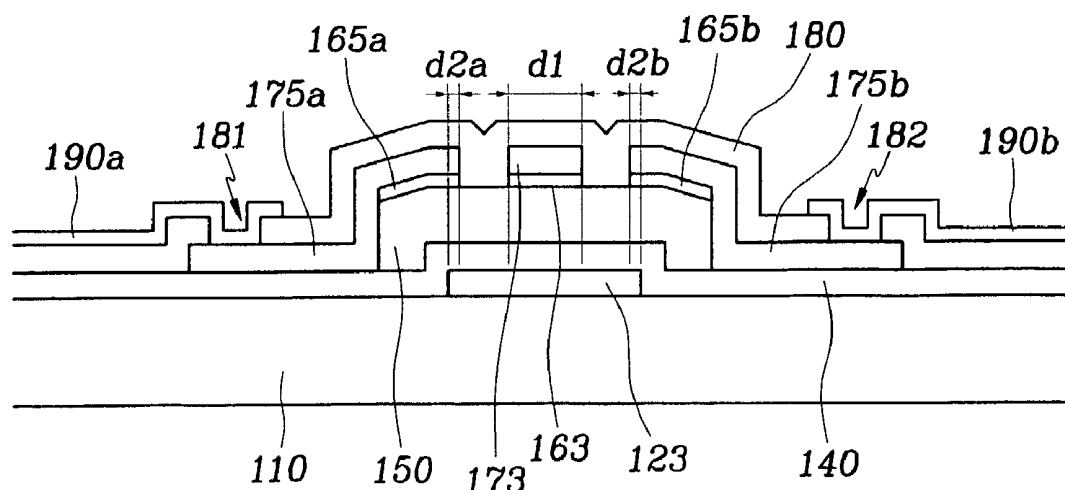
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(57) **ABSTRACT**

A thin film transistor array panel is provided, which includes: an insulating substrate; a gate line formed on the substrate and including a gate electrode; a gate insulating layer formed on the gate line; a semiconductor layer formed on the gate insulating layer opposite the gate electrode; a data line formed on the gate insulating layer and including a first source electrode located on the semiconductor layer; first and second drain electrodes formed on the semiconductor layer, separated from each other and overlapping the gate electrode; a passivation layer formed on the data line and the first and the second drain electrodes; and first and second pixel electrodes electrically connected to the first and the second drain electrodes, respectively, wherein an overlapping area between the gate electrode and the first drain electrode is different from an overlapping area between the gate electrode and the second drain electrode.

14 Claims, 4 Drawing Sheets



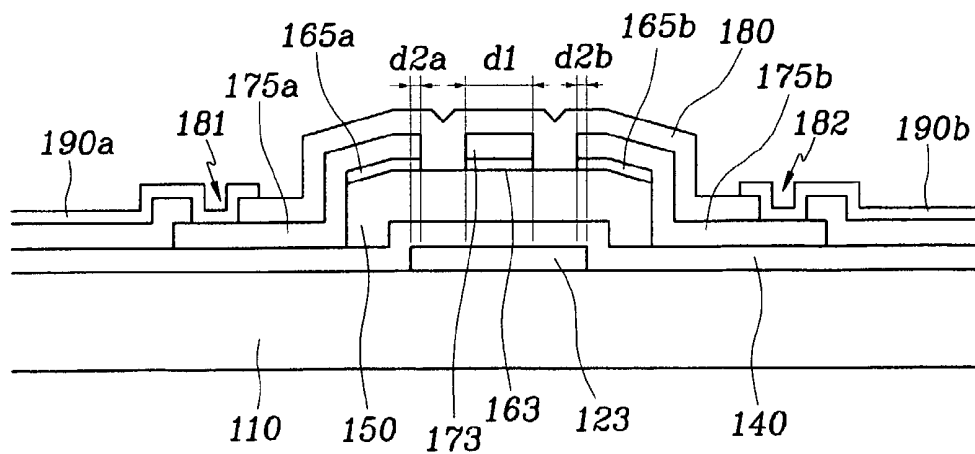


FIG. 3

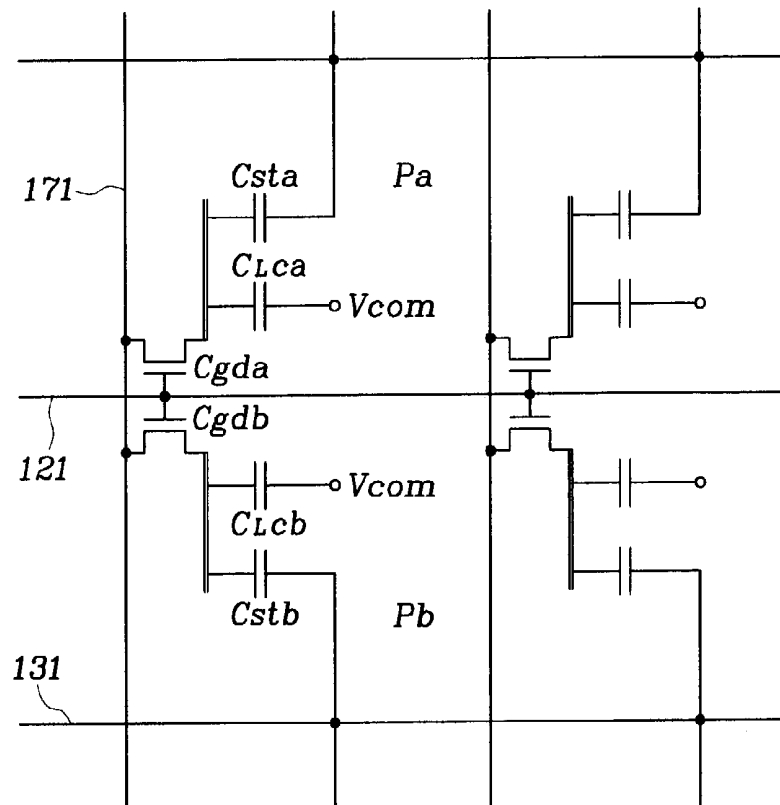


FIG. 4

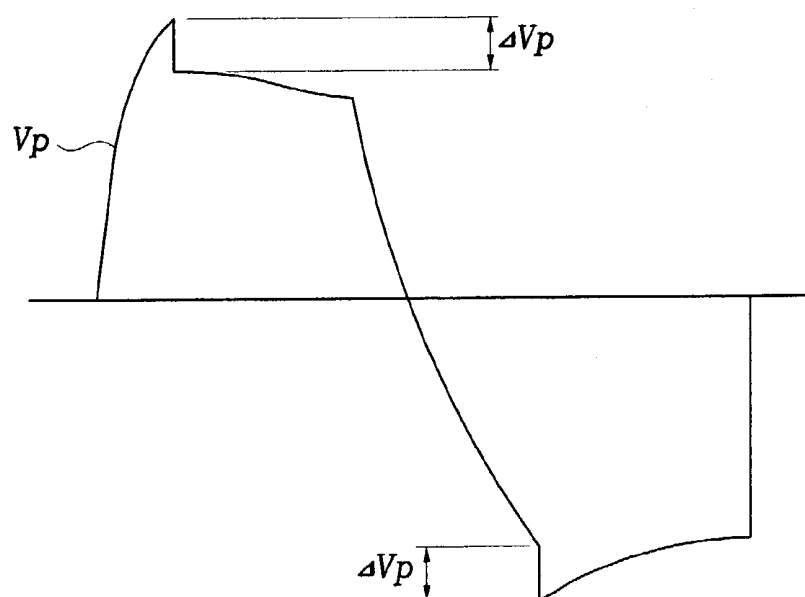
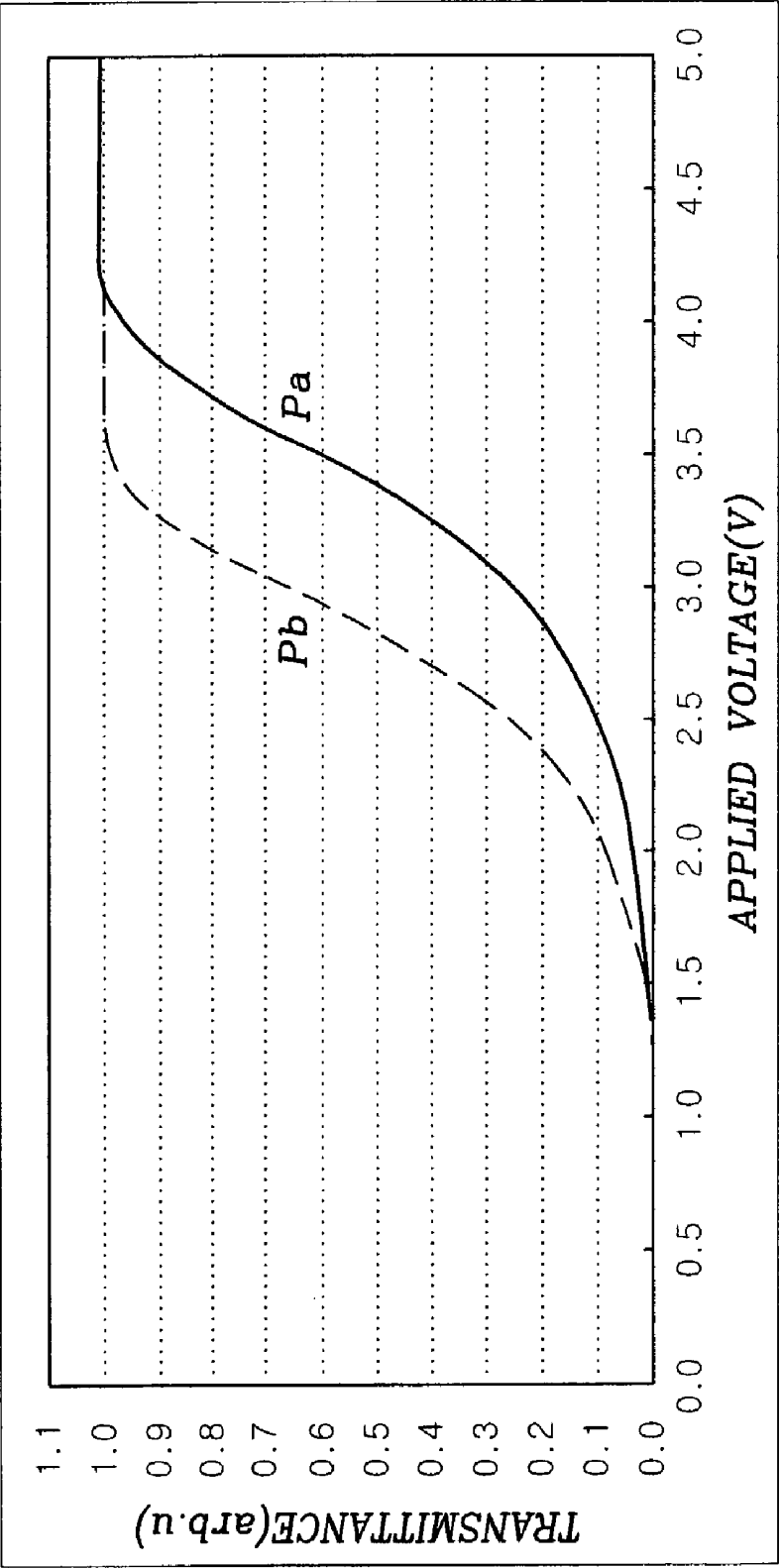
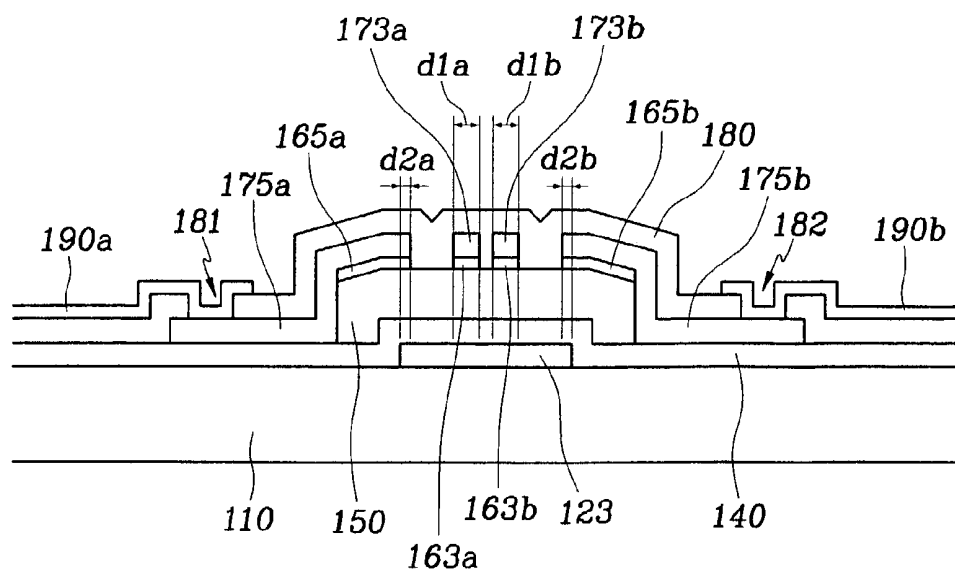


FIG. 5





LIQUID CRYSTAL DISPLAY AND THIN FILM TRANSISTOR ARRAY PANEL THEREFOR

CROSS REFERENCE

This application claims the benefit of Korean Patent Application No. 2002-0070706, filed on Nov. 14, 2002, which is hereby incorporated by reference for all purposes as if fully set forth herein.

BACKGROUND OF THE INVENTION

(a) Field of the Invention

The present invention relates to a liquid crystal display and a thin film transistor array panel therefor.

(b) Description of the Related Art

A typical liquid crystal display ("LCD") includes an upper panel provided with a common electrode and an array of color filters, a lower panel provided with a plurality of thin film transistors ("TFTs") and a plurality of pixel electrodes, and a liquid crystal layer interposed therebetween. The pixel electrodes and the common electrode are supplied with electric voltages and the voltage difference therebetween causes electric field. The variation of the electric field changes the orientations of liquid crystal molecules in the liquid crystal layer, and thus it changes the transmittance of light passing through the liquid crystal layer. As a result, the LCD displays desired images by adjusting the voltage difference between the pixel electrodes and the common electrode.

Since the LCD has disadvantages of narrow viewing angle and poor lateral visibility, several techniques for improving these disadvantages have been developed. Among these techniques, the provision of cutouts or projections on the pixel electrodes and the common electrode opposite each other along with the vertical alignment of the liquid crystal molecules with respect to the panels is promising.

The cutouts provided at the pixel electrodes and the common electrode induce fringe field, which disperses the tilt directions of the liquid crystal molecules to give wide viewing angle. The provision of the projections on the pixel electrode and the common electrode distorts the electric field to adjust the tilt directions of the liquid crystal molecules. The liquid crystal layer of the LCD provided with the cutouts or the protrusions is divided into a plurality of domains based on the tilt directions of the liquid crystal molecules.

However, the lateral visibility of these conventional LCDs is still poor since the tilt angles of the liquid crystal molecules even in the different domains are the same for the same voltages applied to the pixel electrodes.

SUMMARY OF THE INVENTION

A thin film transistor array panel is provided, which includes: first and second signal lines transmitting first and second signals, respectively; first and second switching elements connected to the first and the second signal lines, each of the first and the second switching elements having a first terminal connected to the first signal line, a second terminal connected to the second signal and a third terminal and transmitting the second signal in response to the first signal; and first and second liquid crystal capacitors connected to the third terminals of the first and the second switching elements, respectively, wherein a capacitance

between the first and the third terminals of the first switching element is different from a capacitance between the first and the third terminals of the second switching element.

The liquid crystal display preferably includes first and second storage capacitors connected to the third terminals of the first and the second switching elements in parallel to the first and the second liquid crystal capacitors, respectively.

A thin film transistor array panel is provided, which includes: an insulating substrate; a first signal line provided on the substrate; a second signal line provided on the substrate; first and second thin film transistors connected to the first signal line and the second signal line, each of the first and the second thin film transistors having a first terminal connected to the first signal line, a second terminal connected to the second signal line and a third terminal; and first and second pixel electrodes connected to the third terminals of the first and the second thin film transistors, respectively, wherein a capacitance between the first and the third terminals of the first thin film transistor is different from a capacitance between the first and the third terminals of the second thin film transistor.

Another liquid crystal display is provide, which includes: a first panel including a first insulating substrate, a first signal line provided on the first substrate, a second signal line provided on the first substrate, first and second thin film transistors connected to the first signal line and the second signal line, and first and second pixel electrodes connected to the first and the second thin film transistors, respectively; a second panel facing the first panel and including a second insulating substrate and a common electrode provided on the second substrate; and a liquid crystal layer interposed between the first panel and the second panel, wherein each of the first and the second thin film transistors has a first terminal connected to the first signal line, a second terminal connected to the second signal and a third terminal connected to a corresponding one of the first and the second pixel electrodes, and a capacitance between the first and the third terminals of the first thin film transistor is different from a capacitance between the first and the third terminals of the second thin film transistor.

Another thin film transistor array panel is provided, which includes: an insulating substrate; a gate line formed on the substrate and including a gate electrode;

a gate insulating layer formed on the gate line; a semiconductor layer formed on the gate insulating layer opposite the gate electrode; a data line formed on the gate insulating layer and including a first source electrode located on the semiconductor layer; first and second drain electrodes formed on the semiconductor layer, separated from each other and overlapping the gate electrode; a passivation layer formed on the data line and the first and the second drain electrodes; and first and second pixel electrodes electrically connected to the first and the second drain electrodes, respectively, wherein an overlapping area between the gate electrode and the first drain electrode is different from an overlapping area between the gate electrode and the second drain electrode.

The source electrode may be connected to the first and the second drain electrodes via the semiconductor layer.

Alternatively, the first source electrode is connected to the first drain electrode via the semiconductor layer, and the data line further comprises a second source electrode located on the semiconductor layer and connected to the second drain electrode via the semiconductor layer.

The thin film transistor array panel preferably further includes an ohmic contact layer disposed between the semiconductor layer and the source electrode and the first and the

second drain electrodes and/or a storage electrode overlapping at least one of the first and the second pixel electrodes.

BRIEF DESCRIPTION OF THE DRAWINGS

The above and other advantages of the present invention will become more apparent by describing preferred embodiments thereof in detail with reference to the accompanying drawings in which:

FIG. 1 is a layout view of a TFT array panel for an LCD according to an embodiment of the present invention;

FIG. 2 is a sectional view of the TFT array panel shown in FIG. 1 taken along the line II-II';

FIG. 3 is an equivalent circuit diagram of an LCD including the TFT array panel shown in FIGS. 1 and 2;

FIG. 4 illustrates a pixel voltage of an LCD as function of time;

FIG. 5 shows voltage-transmittance curves for subpixel regions of a normally black mode LCD;

FIG. 6 is a layout view of a TFT array panel for an LCD according to another embodiment of the present invention; and

FIG. 7 is a sectional view of the TFT array panel shown in FIG. 1 taken along the line VII-VII'.

DETAILED DESCRIPTION OF PREFERRED EMBODIMENTS

The present invention now will be described more fully hereinafter with reference to the accompanying drawings, in which preferred embodiments of the inventions invention are shown. The present invention may, however, be embodied in many different forms and should not be construed as limited to the embodiments set forth herein.

In the drawings, the thickness of layers and regions are exaggerated for clarity. Like numerals refer to like elements throughout. It will be understood that when an element such as a layer, region or substrate is referred to as being "on" another element, it can be directly on the other element or intervening elements may also be present. In contrast, when an element is referred to as being "directly on" another element, there are no intervening elements present.

Now, LCDs according to embodiments of this invention will be described in detail with reference to the accompanying drawings.

FIG. 1 is a layout view of a TFT array panel for an LCD according to an embodiment of the present invention, FIG. 2 is a sectional view of the TFT array panel shown in FIG. 1 taken along the line II-II', and FIG. 3 is an equivalent circuit diagram of an LCD including the TFT array panel shown in FIGS. 1 and 2.

A plurality of gate lines **121** and a plurality of storage electrode lines **131** are formed on an insulating substrate **110** preferably made of transparent glass. The gate lines **121** extend substantially in a row direction and substantially parallel to each other and each gate line **121** includes a plurality of expansions forming gate electrodes **123**. The storage electrode lines **131** extend substantially parallel to the gate lines **121** and are supplied with a common voltage V_{com} to be applied to a common electrode (not shown) of another panel (not shown) of an LCD. Each storage electrode **131** may include a plurality of branches (not shown).

The gate lines **121** and the storage electrode lines **131** are preferably made of Al, Cr or their alloys, Mo or Mo alloy. The gate lines **121** and the storage electrode lines **131** preferably include a layer preferably made of Cr or Mo alloys having excellent physical and chemical characteristics

and another layer preferably made of Al or Ag alloys having low resistivity. In addition, the lateral sides of the gate lines **121** are tapered, and the inclination angle of the lateral sides with respect to a horizontal surface ranges 30–80 degrees.

A gate insulating layer **140** is formed on the gate lines **121** and the storage electrode lines **131**.

A plurality of semiconductor islands **150** preferably made of hydrogenated amorphous silicon ("a-Si") are formed on the gate insulating layer **140** and located opposite the gate electrodes **123** with respect to the gate insulating layer **130**. Each semiconductor island **150** forms a channel of TFT.

A plurality of sets of ohmic contacts **163**, **165a** and **165b** preferably made of silicide or hydrogenated a-Si heavily doped with n type impurity such as phosphorous are formed on the semiconductor islands **150**. The lateral sides of the semiconductor islands **150** and the ohmic contacts **163**, **165a** and **165b** are tapered, and the inclination angles thereof are in the range between 30–80 degrees.

A plurality of sets of a data line **171** and a plurality of pairs of first and second drain electrodes **175a** and **175b** are formed on the ohmic contacts **163**, **165a** and **165b**, and the gate insulating layer **140**. The data lines **171** extend substantially in the column direction intersect the gate lines **121** and the storage electrode lines **131**. Each data line **171** includes a plurality of source electrodes **173** extending onto the semiconductor islands **150**. Each pair of the drain electrodes **175a** and **175b** are separated from an associated source electrode **173**, located opposite each other with respect to the source electrode **173**, and extend in opposite directions from an associated semiconductor island **150** on an associated gate electrode **123**.

The data lines **171** and the drain electrodes **175a** and **175b** are preferably made of Al, Cr or their alloys, Mo or Mo alloy. The data lines **171** and the drain electrodes **175a** and **175b** preferably include a layer preferably made of Cr or Mo alloys having excellent physical and chemical characteristics and another layer preferably made of Al or Ag alloys having low resistivity. The data lines **171** and the drain electrodes **175a** and **175b** have tapered lateral sides, and the inclination angles of the lateral sides ranges 30–80 degrees.

The ohmic contacts **163**, **165a** and **165b** are interposed only between the semiconductor islands **150** and the data lines **171** and the drain electrodes **175a** and **175b** to reduce the contact resistance therebetween. Some portions of the semiconductor islands **150** are exposed out of the data lines **171** and the drain electrodes **175a** and **175b**.

The gate electrode **123**, the source electrode **173** and the first drain electrode **175a** along with a portion of the semiconductor island **150** located between the source electrode **173** and the first drain electrode **175a** form a TFT, while the gate electrode **123**, the source electrode **173** and the second drain electrode **175b** along with a portion of the semiconductor island **150** located between the source electrode **173** and the second drain electrode **175b** form another TFT.

Each of the first and the second drain electrodes **175a** and **175b** overlap the gate electrode **123** to form a parasitic capacitor C_{gda} or C_{gdb} . The capacitance of the parasitic capacitor C_{gda} or C_{gdb} is proportional to the overlapping area. According to an embodiment of the present invention, the overlapping area between the first drain electrode **175a** and the gate electrode **123** is different from the overlapping

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area between the second drain electrode **175b** and the gate electrode **123** such that the capacitance between the first drain electrode **175a** and the gate electrode **123** is different from the capacitance between the second drain electrode **175b** and the gate electrode **123**.

A passivation layer **180** preferably made of silicon nitride or organic insulator is formed on the data lines **171** and the drain electrodes **175a** and **175b**, and the exposed portions of the semiconductor islands **150**. The passivation layer **180** is provided with a plurality of first and second contact holes **181** and **182** exposing the first and the second drain electrodes **175a** and **175b**, respectively.

A plurality of pairs of first and second pixel electrodes **190a** and **190b** are formed on the passivation layer **180**. The first and the second pixel electrodes **190a** and **190b** are connected to the first and the second drain electrodes **175a** and **175b** through the first and the second contact holes, respectively. That is, a pair of the first and the second pixel electrodes **190a** and **190b** are connected to respective TFTs connected to the same gate line **121** and the same data line **171**. The first and the second pixel electrodes **190a** and **190b** overlap the storage electrode lines **131** to form storage capacitors **Csta** and **Cstb**, respectively. The pixel electrodes **190a** and **190b** are preferably made of transparent conductive material such as indium zinc oxide ("IZO") and indium tin oxide ("ITO"), or reflective conductive material.

An LCD according to an embodiment of the present invention further includes a common electrode panel (not shown) facing the TFT array panel as well as the TFT array panel and a liquid crystal layer interposed therebetween. The common electrode panel includes a common electrode (not shown) forming a plurality of liquid crystal capacitors **CLCa** and **CLCb** along with the first and the second pixel electrodes **190a** and **190b** of the TFT array panel. As described above, the common electrode is supplied with the common voltage **Vcom**. A polarizer or polarizers (not shown) are attached on outer surfaces of the panels, and a retardation film or films (not shown) may be attached to the outer surface of the common electrode panel.

In circuitual view, an LCD according to this embodiment of the present invention includes a plurality of pixels including two subpixels. Each subpixel includes a TFT including a parasitic capacitor **Cgda** or **Cgdb**, and a liquid crystal capacitor **CLCa** or **CLCb** and a storage capacitor **Csta** or **Cstb** connected to the TFT in parallel as shown in FIG. 3.

When a gate-on voltage **Vg** is applied to a gate line **121** and a data voltage **Vd** is applied to a data line **171**, the TFTs connected to the gate line **121** are turned on and thus the capacitors **CLCa** and **CLCb** connected thereto are charged with pixel voltages **Vpa** and **Vpb**. If the data voltage **Vd** is larger than the common voltage **Vcom**, the pixel voltages **Vpa** and **Vpb** increase during the application of the data voltage **Vd** and are abruptly dropped upon turning off of the TFTs as shown in FIG. 4, which illustrates a pixel voltage **Vp** as function of time. On the contrary, the data voltage **Vd** is smaller than the common voltage **Vcom**, the pixel voltages **Vpa** and **Vpb** decrease during the application of the data voltage **Vd**, and are abruptly increased upon turning off of the TFTs. The voltage drop is called a "kick-back voltage," which is resulted from the parasitic capacitor **Cgda** or **Cgdb**.

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The kick-back voltages ΔV_{pa} and ΔV_{pb} for two respective subpixels are given by:

$$\Delta V_{pa} = V_g \times \frac{C_{gda}}{C_{LCa} + C_{sta} + C_{gda}} \quad (1)$$

$$= V_g \left(1 - \frac{C_{LCa} + C_{sta}}{C_{LCa} + C_{sta} + C_{gda}} \right); \text{ and}$$

$$\Delta V_{pb} = V_g \times \frac{C_{gdb}}{C_{LCb} + C_{stb} + C_{gdb}} \quad (2)$$

$$= V_g \left(1 - \frac{C_{LCb} + C_{stb}}{C_{LCb} + C_{stb} + C_{gdb}} \right).$$

where the capacitors and their capacitances are indicated by the same reference numerals.

As shown in Equations (1) and (2), the kick-back voltage increases as the parasitic capacitance increases and vice versa.

According to this embodiment, the parasitic capacitance **Cgda** is different from the parasitic capacitance **Cgdb** and thus the kick-back voltage ΔV_{pa} is different from the kick-back voltage ΔV_{pb} since the overlapping area between the first drain electrode **175a** and the gate electrode **123** is different from the overlapping area between the second drain electrode **175b** and the gate electrode **123** as described above.

Referring to FIG. 2, the overlapping areas are adjusted by changing the overlapping width while maintaining the overlapping length to be constant. In this embodiment, the overlapping width **d2a** between the first drain electrode **175a** and the gate electrode **123** is different from the overlapping width **d2b** between the second drain electrode **175b** and the gate electrode **123**.

Accordingly, the pixel voltage **Vpa** is different from the pixel voltage **Vpb**.

It is noted that the kick-back voltages ΔV_{pa} and ΔV_{pb} are as small as possible since the kick-back voltages may generate afterimage and flicker. A measured value of a kick-back voltage upon application of a data voltage **Vd** of 10 V was about 0.5 V to 1.0 V, which was expected to be about 0.8 V to 0.9 V through a simulation.

The difference of the pixel voltages **Vpa** and **Vpb** differentiates the strength of electric fields in respective subpixel regions **Pa** and **Pb**, which are portions of the liquid crystal layer located on the first and the second pixel electrodes **190a** and **190b**, respectively. The different field strength in turn differentiates the tilt angles of liquid crystal molecules in the subpixel regions **Pa** and **Pb**.

FIG. 5 shows voltage-transmittance (V-T) curves for the subpixel regions **Pa** and **Pb** of a normally black mode LCD, which are different from each other. The V-T curve for the subpixel region **Pa** with a larger parasitic capacitance **Cgda** underlies that for the subpixel region **Pb** with a smaller parasitic capacitance **Cgdb**.

Accordingly, the characteristics of the subpixel regions **Pa** and **Pb** effectively compensate each other to widen the viewing angle of the LCD. The LCD may be in a vertically aligned (VA) mode, twisted-nematic (TN) mode or optical-compensated bend (OCB) mode.

Now, an LCD according to another embodiment of the present invention is described in detail with reference to FIGS. 6-8.

FIG. 6 is a layout view of a TFT array panel for an LCD according to another embodiment of the present invention,

and FIG. 7 is a sectional view of the TFT array panel shown in FIG. 1 taken along the line VII-VII'.

Referring to FIGS. 6 and 7, a TFT array panel according to this embodiment includes a plurality of gate lines 121 and a plurality of storage electrode lines 131 formed on an insulating substrate 110, a gate insulating layer 140 formed on the gate lines 121 and the storage electrode lines 131, and a plurality of semiconductor islands 150 formed on the gate insulating layer 140.

A plurality of ohmic contacts 163a, 163b, 165a and 165b are formed on the semiconductor islands 150.

A plurality of sets of a data line 171 and a plurality of pairs of first and second drain electrodes 175a and 175b are formed on the ohmic contacts 163, 165a and 165b, and the gate insulating layer 140. Each data line 171 includes a plurality of first and second source electrodes 173a and 173b extending onto the semiconductor islands 150. Each of the first and the second drain electrodes 175a and 175b are separated from the first and the second source electrodes 173a and 173b. The first source electrode 173a and the first drain electrode 175a face each other while the second source electrode 173b and the second drain electrode 175b faces each other.

The gate electrode 123, the first source electrode 173a and the first drain electrode 175a along with a portion of the semiconductor island 150 located between the first source electrode 173a and the first drain electrode 175a form a TFT, while the gate electrode 123, the second source electrode 173b and the second drain electrode 175b along with a portion of the semiconductor island 150 located between the second source electrode 173b and the second drain electrode 175b form another TFT.

According to this embodiment of the present invention, the overlapping areas between the first drain electrode 175a and the gate electrode 123 and between the second drain electrode 175b and the gate electrode 123 are different such that the capacitance between the first drain electrode 175a and the gate electrode 123 is different from the capacitance between the second drain electrode 175b and the gate electrode 123.

A passivation layer 180 is formed on the data lines 171 and the drain electrodes 175a and 175b, and the semiconductor islands 150. The passivation layer 180 is provided with a plurality of first and second contact holes 181 and 182 exposing the first and the second drain electrodes 175a and 175b, respectively. A plurality of pairs of first and second pixel electrodes 190a and 190b are formed on the passivation layer 180. The first and the second pixel electrodes 190a and 190b are connected to the first and the second drain electrodes 175a and 175b through the first and the second contact holes, respectively. That is, a pair of the first and the second pixel electrodes 190a and 190b are connected to respective TFTs connected to the same gate line 121 and the same data line 171. The first and the second pixel electrodes 190a and 190b overlap the storage electrode lines 131 to form storage capacitors Csta and Cstb, respectively.

According to this embodiment, the parasitic capacitance Cgda is different from the parasitic capacitance Cgdb and thus the kick-back voltage ΔV_{pa} is different from the kick-back voltage ΔV_{pb} since the overlapping area between the first drain electrode 175a and the gate electrode 123 is different from the overlapping area between the second drain electrode 175b and the gate electrode 123 as described above.

Referring to FIG. 7, the overlapping width d2a between the first drain electrode 175a and the gate electrode 123 is

different from the overlapping width d2b between the second drain electrode 175b and the gate electrode 123.

Accordingly, the pixel voltage V_{pa} is different from the pixel voltage V_{pb} , and V-T curves for subpixel regions Pa and Pb on the first and the second pixel electrodes 190a and 190b are different from each other. Therefore, the characteristics of the subpixel regions Pa and Pb effectively compensate each other to widen the viewing angle of the LCD.

Although preferred embodiments of the present invention have been described in detail hereinabove, it should be clearly understood that many variations and/or modifications of the basic inventive concepts herein taught which may appear to those skilled in the present art will still fall within the spirit and scope of the present invention, as defined in the appended claims.

What is claimed is:

1. A liquid crystal display, comprising:

a gate lines transmitting a gate signal;

a data line transmitting a data signal;

a first switching element comprising a first terminal connected to the gate line, a second terminal connected to the data line and a third terminal;

a second switching element comprising a first terminal connected to the gate signal line, a second terminal connected to the data line and a third terminal;

a first liquid crystal capacitors connected to the third terminal of the first switching element; and

a second crystal capacitor connected to the third terminal of the second switching element,

wherein a capacitance between the first and the third terminal of the first switching element is different from that between the first terminal and the third terminals of the second switching element.

2. The liquid crystal display of claim 1, further comprising:

a first storage capacitor connected to the third terminal of the first switching element; and

a second storage capacitor connected to the third terminal of the second switching element.

3. A thin film transistor array panel, comprising:

an insulating substrate;

a gate line provided on the substrate;

a data line provided on the substrate;

first thin film transistors comprising a first terminal connected to the gate line, a second terminal connected to the data line and a third terminal;

a second thin film transistor comprising a first terminal connected to the gate line, a second terminal connected to the data line and a third terminal;

a first pixel electrode connected to the third terminal of the first film transistor; and

a second pixel electrode connected to the third terminal of the second thin film transistor,

wherein a capacitance between the first terminal and the third terminal of the first thin film transistor is different from that between the first terminal and the third terminal of the second thin film transistor.

4. A liquid crystal display, comprising:

a first panel including:

a first insulating substrate;

a gate line provided on the first substrate;

a data line provided on the first substrate;

a first thin film transistors comprising a first terminal connected to the gate line, a second terminal connected to the data line and a third terminal;

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a second thin film transistor comprising a first terminal connected to the gate line, a second terminal connected to the data line and a third terminal; a first pixel electrode connected to the third terminal of the first thin film transistor; and a second pixel electrode connected to the third terminal of the second thin film transistor;

a second panel facing the first panel and including a second insulating substrate and a common electrode provided on the second substrate; and

a liquid crystal layer interposed between the first panel and the second panel,

wherein a capacitance between the first and third terminals of the first thin film transistor is different from a capacitance between the first and third terminals of the second thin film transistor.

5 **5.** A thin film transistor array panel, comprising:
an insulating substrate;
a gate line formed on the substrate and including a gate electrode;

10 a gate insulating layer formed on the gate line;
a semiconductor layer formed on the gate insulating layer opposite the gate electrode;
a data line formed on the gate insulating layer and including a first source electrode located on the semiconductor layer;

15 first and second drain electrodes formed on the semiconductor layer, separated from each other and overlapping the gate electrode;

20 a passivation layer formed on the data line and the first and the second drain electrodes; and
first and second pixel electrodes electrically connected to the first and the second drain electrodes, respectively, wherein an overlapping area between the gate electrode and the first drain electrode is different from an overlapping area between the gate electrode and the second drain electrode.

25 **6.** The thin film transistor array panel of claim **5**, wherein the source electrode is connected to the first and the second drain electrodes via the semiconductor layer.

30 **7.** The thin film transistor array panel of claim **5**, wherein the first source electrode is connected to the first drain electrode via the semiconductor layer, and the data line further comprises a second source electrode located on the semiconductor layer and connected to the second drain electrode via the semiconductor layer.

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8. The thin film transistor array panel of claim **5**, further comprising an ohmic contact layer disposed between the semiconductor layer and the source electrode and the first and the second drain electrodes.

5 **9.** The thin film transistor array panel of claim **5**, further comprising a storage electrode overlapping at least one of the first and the second pixel electrodes.

10. A pixel of a display device, comprising:

a gate line;

a data line intersecting the gate line;

a switching unit comprising:

a gate electrode connected to the gate line;

a source electrode connected to the data line;

a first drain electrode; and

a second drain electrode;

a first pixel electrode connected to the first drain electrode; and

a second pixel electrode connected to the second drain electrode,

wherein two different voltages are applied to the first pixel electrode and the second pixel electrode, respectively, when the switching unit is turned on.

11. The pixel of claim **10**, wherein the gate electrode and the first drain electrode form a first capacitance and the gate electrode and the second drain electrode form a second capacitance, the first capacitance being different from the second capacitance.

12. The pixel of claim **10**, wherein a size of an overlapped portion between the first pixel electrode and the gate electrode is different from that of the overlapped portion between the second pixel electrode and the gate electrode.

13. The pixel of claim **10**, further comprising:

a common electrode provided corresponding to the first and second pixel electrode with a gap therebetween; and

liquid crystal molecules disposed in the gap,

wherein twist angles of the liquid crystal molecules are differentiated by the two different voltages applied to the first and second pixel electrodes, respectively.

14. The pixel electrode of claim **10**, wherein the gate line is extending between the first pixel electrode and the second pixel electrode.

* * * * *

专利名称(译)	液晶显示器及其薄膜晶体管阵列面板		
公开(公告)号	US6999134	公开(公告)日	2006-02-14
申请号	US10/445849	申请日	2003-05-28
[标]申请(专利权)人(译)	三星电子株式会社		
申请(专利权)人(译)	SAMSUNG ELECTRONICS CO. , LTD.		
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IPC分类号	G02F1/1343 G02F1/1333 G02F1/136 G02F1/1362 G02F1/1368 G09F9/30 G09F9/35 H01L27/12 H01L27/13		
CPC分类号	G02F1/13624 H01L27/1255 G02F1/1368 G02F2001/134345		
优先权	1020020070706 2002-11-14 KR		
其他公开文献	US20040094766A1		
外部链接	Espacenet USPTO		

摘要(译)

提供一种薄膜晶体管阵列面板，包括：绝缘基板；栅极线形成在基板上并包括栅极电极；栅极绝缘层形成在栅极线上；半导体层形成在与栅电极相对的栅极绝缘层上；数据线，形成在栅极绝缘层上，并包括位于半导体层上的第一源电极；第一和第二漏电极形成在半导体层上，彼此分开并与栅电极重叠；形成在数据线和第一和第二漏电极上的钝化层；第一和第二像素电极分别电连接到第一和第二漏电极，其中栅电极和第一漏电极之间的重叠区域不同于栅电极和第二漏电极之间的重叠区域。

